

## Features

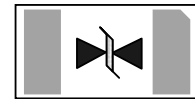
100Watts peak pulse power ( $t_p = 8/20\mu s$ )  
 Tiny DFN1006 package  
 Bidirectional configurations  
 Solid-state silicon-avalanche technology  
 Low clamping voltage  
 Low leakage current  
 Low capacitance ( $C_j = 0.3pF$  typ. IO to IO)  
 IEC 61000-4-2  $\pm 20kV$  contact  $\pm 20kV$  air  
 IEC 61000-4-4 (EFT) 40A  $\bar{3}(50ns)$   
 IEC 61000-4-5 (Lightning) 4.5A ( $8/20\mu s$ )

## Applications

Cell Phone Handsets and Accessories  
 Microprocessor based equipment  
 Personal Digital Assistants (PDA's)  
 Notebooks, Desktops, and Servers  
 Portable Instrumentation



DFN1006-2L(Pb-Free)



Schematic Diagram

## Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{pp}$	100	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ ) (note1)	$I_{pp}$	4.5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{ESD}$	20 20	kV
Lead Soldering Temperature	$T_L$	260(10seconds)	$^{\circ}C$
Junction Temperature	$T_J$	-55 to + 125	$^{\circ}C$
Storage Temperature	$T_{stg}$	-55 to + 125	$^{\circ}C$

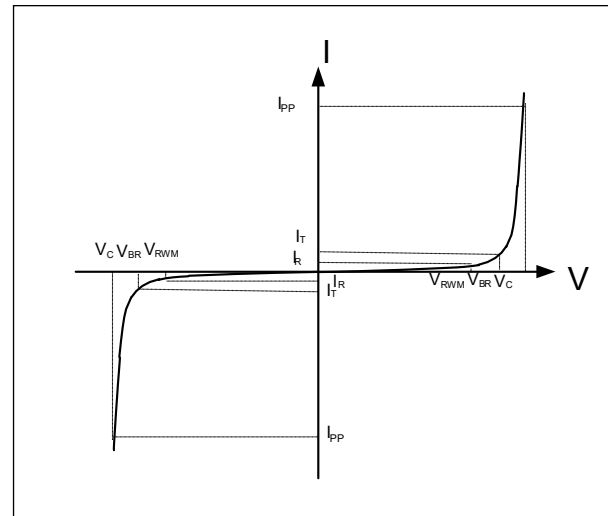
**Electrical Characteristics** (TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1mA$	6.0			V
Reverse Leakage Current	$I_R$	$V_{RWM}=5V, T=25^\circ C$			100	nA
Peak Pulse Current	$I_{PP}$	$t_p=8/20\mu s$			4.0	A
Clamping Voltage	$V_C$	$I_{PP}=4.5A, t_p=8/20\mu s$			20	V
Junction Capacitance	$C_j$	IO to IO $V_R=0V, f=1MHz$		0.3		pF

**Electrical Parameters** (TA = 25°C unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current

Note: 8/20μs pulse waveform.



Typical Performance Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise Specified)

Figure 1: Peak Pulse Power vs. Pulse Time

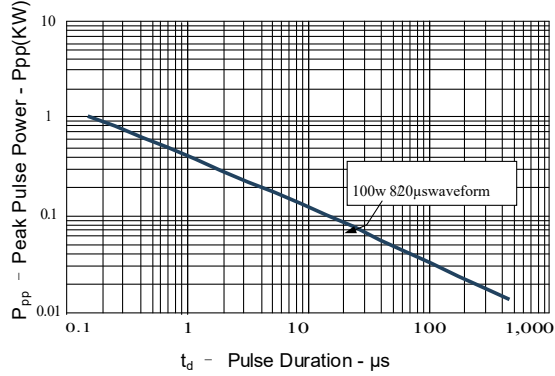


Figure 2: Power Derating Curve

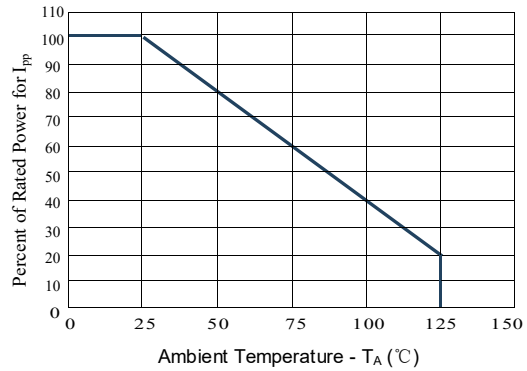


Figure3: Pulse Waveform

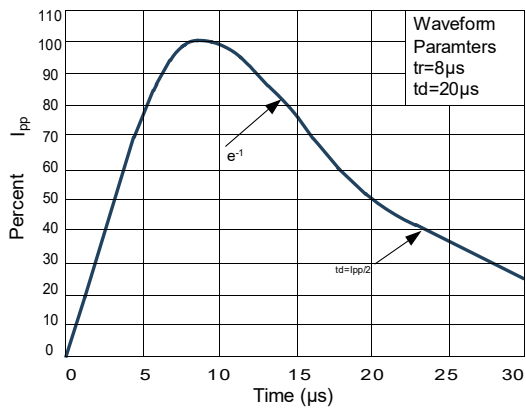


Figure 4: Clamping Voltage vs. Ipp

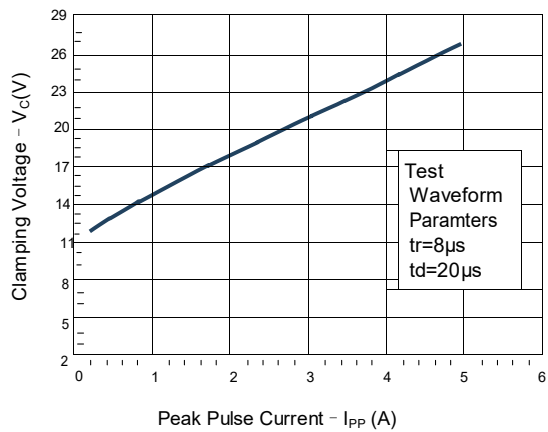


Figure5: Positive Clamping voltage (TLP)

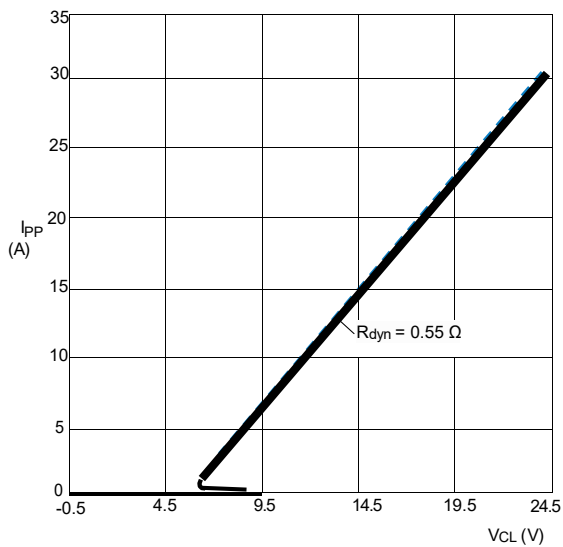
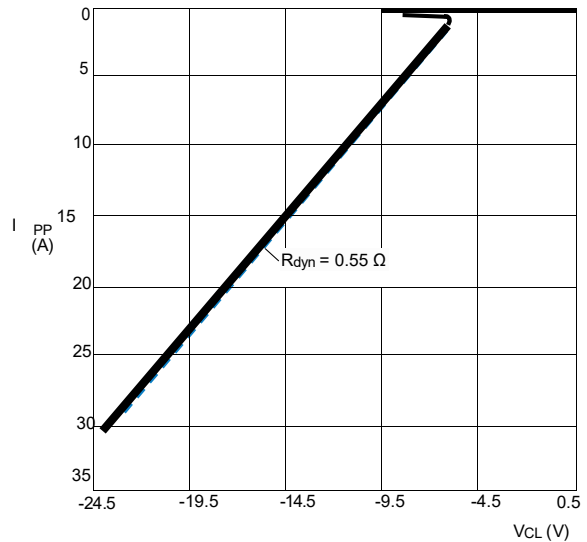


Figure5: Negative Clamping voltage (TLP)



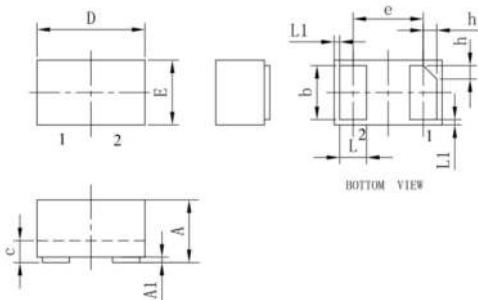
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ )(Liquid us)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_P$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260°C



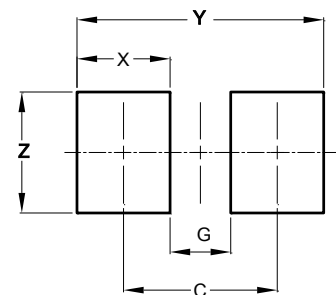
Package Dimensions & Suggested Pad Layout

DFN1006-2L



DFN1006-2L

	Millimeters			Inches		
	Min. (mm)	Typ. (mm)	Max. (mm)	Min. (mm)	Typ. (mm)	Max. (mm)
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.59BSC			0.026BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.25	0.30	0.35	0.010	0.012	0.013
L1	0.05REF			0.002REF		
h	0.07	0.12	0.17	0.003	0.005	0.007



Dimensions	Value (in mm)
C	0.70
G	0.30
X	0.40
Y	1.10
Z	0.65

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.20
		P1	2.00±0.20
		P2	1.55±0.20
		D0	1.55±0.20
		D1	0.40±0.20
		E	1.55±0.25
		F	3.60±0.20
		W	8.00±0.20
		A0	1.00±0.20
		B0	1.40±0.20
		K0	0.75±0.20
		T	0.20±0.20
		D2	177.0±5.0
		D3	55Min.
		D4	R24.6±2.0
G	R82.0±2.0		
I	13.0±2.0		
W1	10.20±3.0		
Quantity: 3000PCS			

7" Reel

